TOSHIBA GT15J121

Preliminary

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Chanenel IGBT

GT15J121

High Power Switching Applications

Fast Switching Applications

The 4th generation

Enhancement-mode

Ultra Fast Switching(UFS : Operating frequency up to 150kHz(Reference)

· High speed

 $:t_r=0.03 \,\mu \,s(typ.)$

 $:t_f=0.08 \,\mu \,s(typ.)$

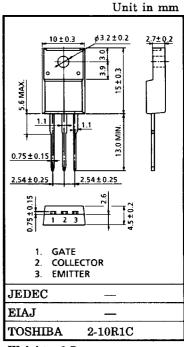
• Low switching loss

 $:E_{on}=0.23$ mJ(typ.)

 $:E_{off}=0.18mJ(typ.)$

Maximum Ratings (Ta=25°C)

Characteristic		Symbol	Ratings	Unit	
Collector-emitter voltage		V_{CES}	600	V	
Gate-emitter voltage		V_{GES}	±20	V	
Collector current	DC	I_{C}	15	Α	
	1ms	I_{CP}	45		
Collector power dissipation		P _C	35	W	
(Tc=25°C)		٠ ٢	00		
Junction temperature		T_{j}	150	°C	
Storage temperature range		T_{stg}	-55 ∼ 150	°C	



Weight: 1.7g

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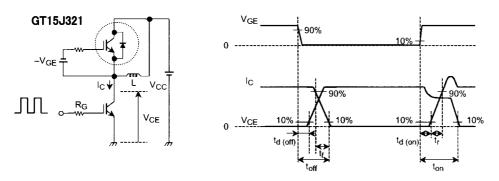
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Electrical Characteristics(Ta=25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		\mathbf{I}_{GES}	$V_{GE}=\pm 20V, V_{CE}=0$	_	_	±500	nΑ
Collector cut-off current		I _{CES}	V _{CE} =600V,V _{GE} =0	_	_	1.0	mA
Gate-emitter cut-off voltage		$V_{GE(OFF)}$	I_C =1.5mA, V_{CE} =5V	3.0	-	6.0	V
Collector-emitter saturation volatage		$V_{CE(sat)}$	I _C =15A,V _{GE} =15V	_	2.7	3.5	V
Input capacitance		C _{ies}	V _{CE} =10V,V _{GE} =0,f=1MHz	_	1300	-	pF
Switching time	Turn-on delay time	$t_{d(on)}$	Inductive Load V _{CC} =300V,I _C =15A	_	0.04	-	μs
	Rise Time	t _r		_	0.03	-	
	Turn-on Time	t _{on}		_	0.12	-	
	Turn-off delay time	$t_{d(off)}$	V_{GG} =+15V, R_{G} =27 Ω	_	0.10	-	
	Fall Time	t_f	(Note 1)	_	0.08	0.15	
	Turn-off Time	t_{off}	(Note 2)	_	0.20	-	
Switching loss	Turn-on switching loss	E _{on}		_	0.23	-	mJ
	Turn-off switching loss	E_{off}		_	0.18	_	
Thermal resistance		$R_{th(j-c)}$	_	_	_	3.57	°C/W

Note1: Switching time measurement circuit and input/output waveforms



Note 2: Switching loss measurement waveforms

